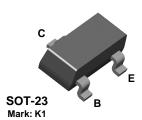


### **BCW71**



## **NPN General Purpose Amplifier**

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 10.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
V <sub>CES</sub>	Collector-Base Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage 5.0		V
Ic	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		*BCW71		
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

<sup>\*</sup>Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

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### **NPN General Purpose Amplifier**

(continued)

Electr	ical	Cha	racte	ristic	S
		9:::4		,,,,,,,,	•

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
OFF CHARACTERISTICS						
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 1.0 \text{ mA}, I_B = 0$	45			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	50			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0			V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 20 \text{ V}, I_E = 0$ $V_{CB} = 20 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$			100 10	μΑ

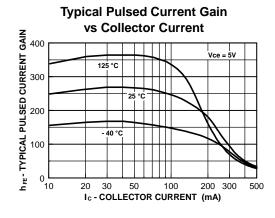
### **ON CHARACTERISTICS**

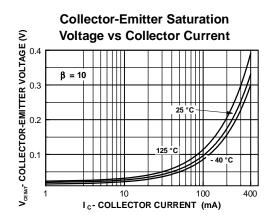
h <sub>FE</sub>	DC Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	110		220	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$			0.25	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$		0.85		V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	0.6		0.75	V

### SMALL SIGNAL CHARACTERISTICS

f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 35 MHz	330		MHz
C <sub>obo</sub>	Output Capacitance	$V_{CE} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		4.0	pF
C <sub>ibo</sub>	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$	9.0		pF
NF	Noise Figure	$\begin{split} I_C &= 0.2 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ R_S &= 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz}, \\ BW &= 200 \text{ Hz} \end{split}$		10	dB

### **Typical Characteristics**

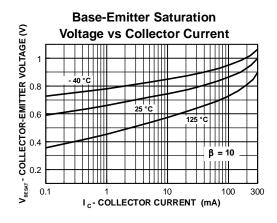


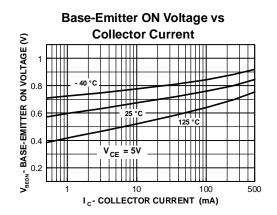


### **NPN General Purpose Amplifier**

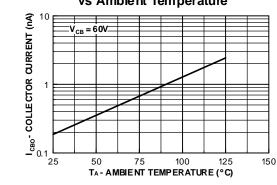
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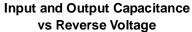
### Typical Characteristics (continued)

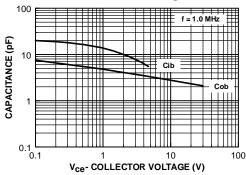




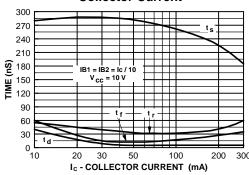
# Collector-Cutoff Current vs Ambient Temperature



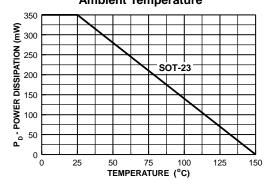




Switching Times vs Collector Current



Power Dissipation vs Ambient Temperature



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Rev. G